

Product Summary

$V_{(BR)DSS}$	$R_{DS(on)TYP}$	I_D
60V	1.2Ω@10V	0.41A
	1.3Ω@4.5V	

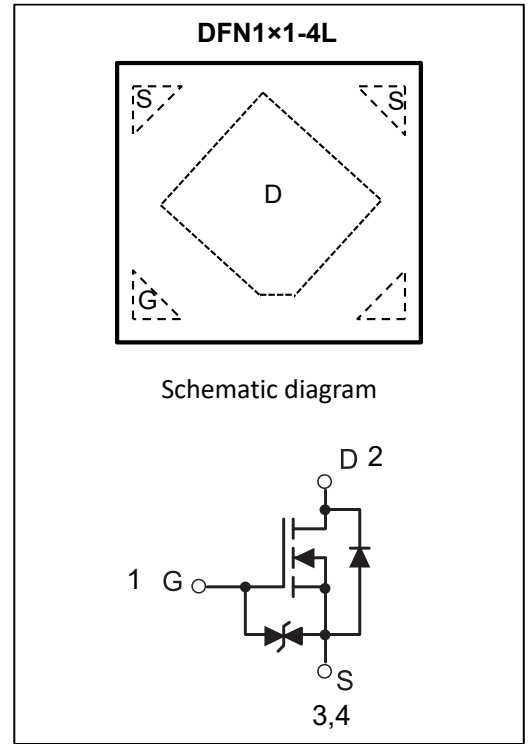
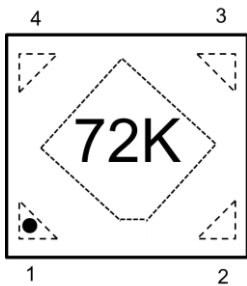
Feature

- Low On-Resistance
- Low Threshold Voltage
- Fast Switching Speed
- ESD Protected Gate

Application

- Load Switch
- Portable Applications
- Power Management Functions

MARKING:



ABSOLUTE MAXIMUM RATINGS ($T_a=25^{\circ}C$ unless otherwise noted)

Parameter	Symbol	Value	Unit
Drain-Source Voltage	V_{DS}	60	V
Gate-Source Voltage	V_{GS}	±20	V
Continuous Drain Current	I_D	$T_a=25^{\circ}C$	0.41
		$T_a=85^{\circ}C$	0.30
Pulsed Drain Current	I_{DM}	1.2	A
Power Dissipation	P_D	0.2	W
Thermal Resistance from Junction to Ambient	$R_{\theta JA}$	625	$^{\circ}C/W$
Storage Temperature	T_{STG}	-55~ +150	$^{\circ}C$

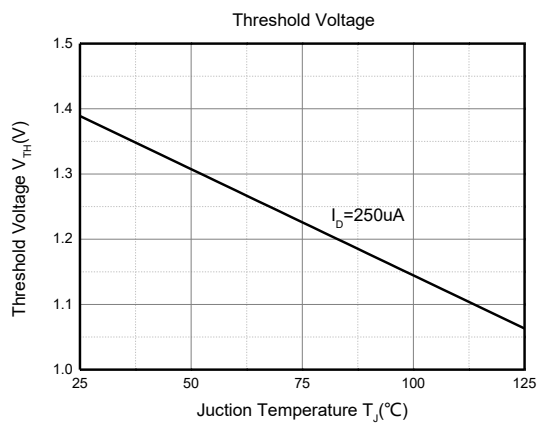
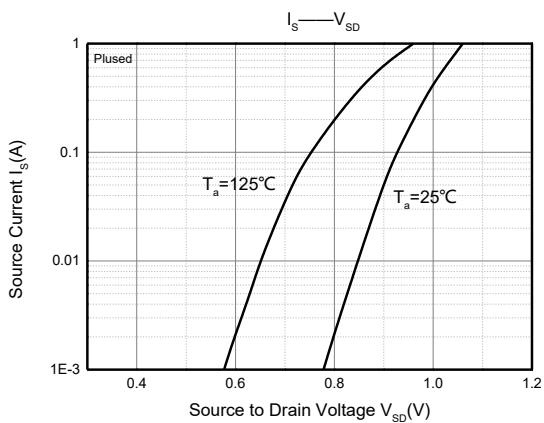
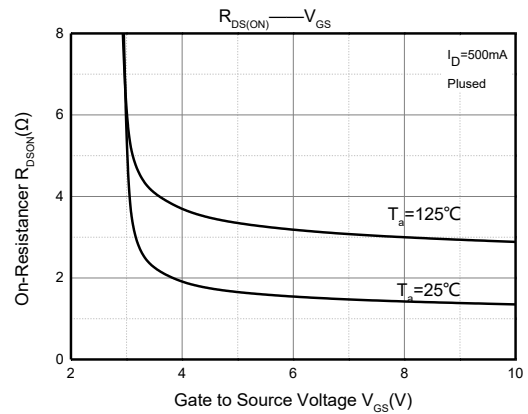
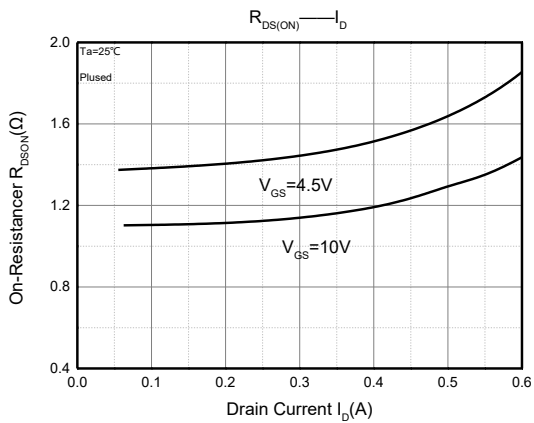
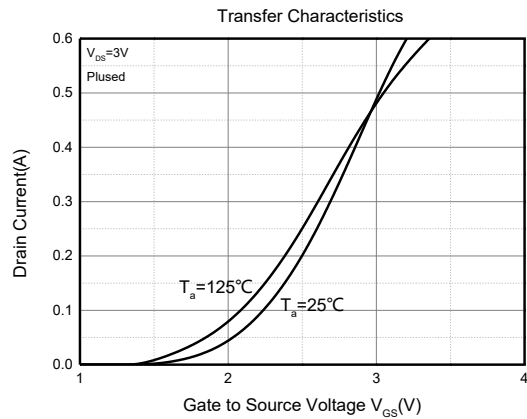
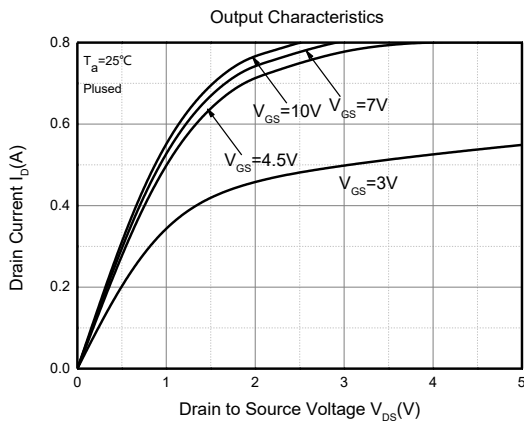
MOSFET ELECTRICAL CHARACTERISTICS(T_a=25°C unless otherwise noted)

Parameter	Symbol	Test Condition	Min	Type	Max	Unit
Static Characteristics						
Drain-source breakdown voltage	V _{(BR)DSS}	V _{GS} = 0V, I _D = 250μA	60			V
Zero gate voltage drain current	I _{DSS}	V _{DS} = 60V, V _{GS} = 0V			100	nA
Gate-body leakage current	I _{GSS}	V _{GS} = ±20V, V _{DS} = 0V			±10	μA
		V _{GS} = ±5V, V _{DS} = 0V			±1	
Gate threshold voltage	V _{GS(th)}	V _{DS} = V _{GS} , I _D = 250μA	1.0	1.4	2.5	V
Drain-source on-resistance ^a	R _{DS(on)}	V _{GS} = 10V, I _D = 40mA		1.2	1.5	Ω
		V _{GS} = 4.5V, I _D = 35mA		1.3	1.8	
Forward tranconductance ^a	g _{fs}	V _{DS} = 5V, I _D = 40mA	100			mS
Diode forward voltage	V _{SD}	V _{DS} = 0V, I _S = 300mA		0.84	1.1	V
Dynamic characteristics						
Input Capacitance ^b	C _{iss}	V _{DS} = 40V, V _{GS} = 0V, f = 1MHz		41	80	pF
Output Capacitance ^b	C _{oss}			3.6	7	
Reverse Transfer Capacitance ^b	C _{rss}			2.9	5.6	
Gate resistance	R _g	V _{DS} = 0V, V _{GS} = 0V, f = 1MHz		81	200	Ω
Total Gate Charge	Q _g	V _{GS} = 4.5V	V _{DS} = 50V, I _D = 1A	0.72	1.5	nC
		V _{GS} = 10V		1.41	2.8	
Gate-Source Charge	Q _{gs}			0.24	0.4	
Gate-Drain Charge	Q _{gd}			0.24	0.5	
Turn-on delay time ^b	t _{d(on)}	V _{DS} = 50V, I _D = 1A, V _{GS} = 10V, R _G = 6Ω		3.98	10	ns
Turn-on rise time ^b	t _r			4.95	10	
Turn-off delay time ^b	t _{d(off)}			18.52	40	
Turn-off fall time ^b	t _f			11.94	25	

Notes:

- a. Pulse Test : Pulse width ≤ 300μs, duty cycle ≤ 2%.
b. These parameters have no way to verify.

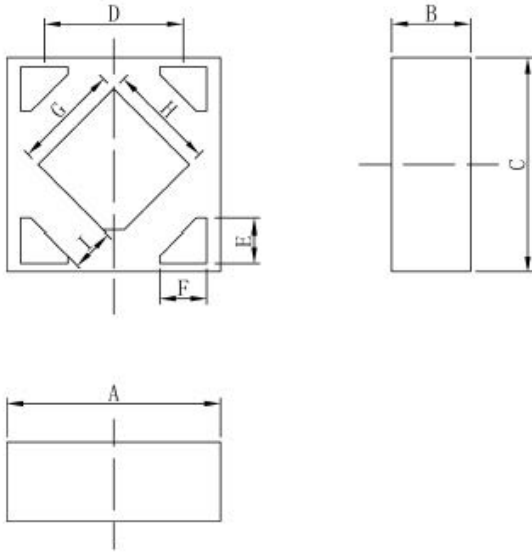
Typical Electrical and Thermal Characteristics



DFN1×1-4L Package Information

DFN1 × 1-4L (0.49 × 0.49)

Unit:mm



Dimensions In Millimeterer			
Symbol	MIN	TYP	MAX
A	0.950	1.000	1.050
B	0.320	0.370	0.420
C	0.950	1.000	1.050
D	0.600	0.650	0.700
E	0.175	0.225	0.275
F	0.170	0.220	0.270
G	0.440	0.490	0.540
H	0.440	0.490	0.540
I	0.140	0.190	0.240

单击下面可查看定价，库存，交付和生命周期等信息

[>>GP\(格瑞宝\)](#)